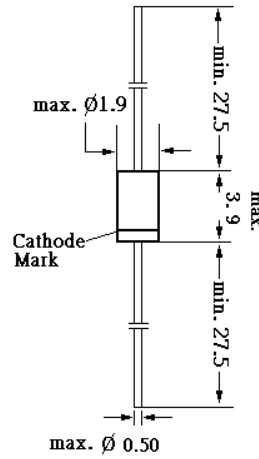


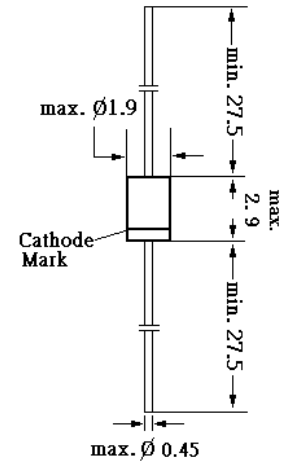
1N914...1N4454

SILICON EPITAXIAL PLANAR DIODES
for general purpose and switching

The types 1N4149, 1N4447 and 1N4449 are
also available in glass case DO-34.



Glass case JEDEC DO-35
Dimensions in mm



Glass case JEDEC DO-34
Dimensions in mm

Type	Peak reverse voltage $V_{RM}V$	Max. aver. rectified current $I_{OM}A$	Max. power dissip. at 25? $P_{tot}mW$	Max. junction temperature $T_j ^\circ C$	Max. forward voltage drop V_FV	Max. reverse current			Max. reverse recovery time	
						at I_F mA	at I_n nA	at V_RV	$t_{rr}ns$	Conditions
1N914	100	75	500	200	1	10	25	20	Max.4	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4149 ¹⁾	100	150	500	200	1	10	25	20	Max.4	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4151	75	150	500	200	1	50	50	50	Max.2	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4152	40	150	400	175	0.55	0.1	50	30	Max.2	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4153	75	150	400	175	0.55	0.1	50	50	Max.2	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4154	35	150 ²⁾	500	200	1	30	100	25	Max.2	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4447 ¹⁾	100	150	500	200	1	20	25	20	Max.4	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4449 ¹⁾	100	150	500	200	1	30	25	20	Max.4	$I_F=10mA, V_R=6V, R_L=100 \Omega, I_R=1mA$
1N4450	40	150	400	175	0.54	0.5	50	30	Max.4	$I_F=I_R=10mA, I_R=1mA$
1N4451	40	150	400	175	0.5	0.1	50	30	Max.10	$I_F=I_R=10mA, I_R=1mA$
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1	10	100	50	Max.4	$I_F=I_R=10mA, I_R=1mA$

1). These diodes are also available in glass case DO-34.

2). Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

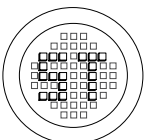
Parameters for diodes in case DO-34:

$$P_{tot} = 300mW$$

$$T_s = -65 \text{ to } +175^\circ C$$

$$T_j = 175^\circ C$$

$$R_{thA} = \leq 0.4 \text{ K/mW}$$



®

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